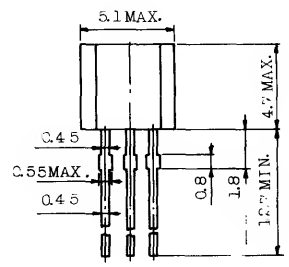
SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

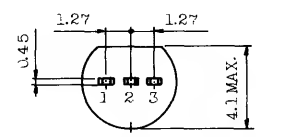
TBC327
TBC328

PRIMARILY INTENDED FOR USE IN DRIVER
AND OUTPUT STAGE OF AUDIO AMPLIFIERS.
NPN COMPLEMENTS ARE TBC337 AND TBC338.

FEATURES:
. High V_{CEO} : -45V (TBC327)
-25V (TBC328)
. Low Saturation Voltage
: $V_{CE(sat)}$=-0.7V (Max.) at I_C=-500mA

Unit in mm





1. COLLECTOR
2. BASE
3. EMITTER

JEDEC	TO-92
EIAJ	SC-43
TOSHIBA	2-5F1G

Weight : 0.21g

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Breakdown Voltage	TBC327	$V_{(BR)CBO}$	-50	V
	TBC328		-30	
Collector-Emitter Breakdown Voltage	TBC327	$V_{(BR)CEO}$	-45	V
	TBC328		-25	
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	-5	V
Collector Current	DC	I_C	-500	mA
	Peak	I_{CP}	-1000	
Base Current (DC)		I_B	-100	mA
Collector Power Dissipation		P_C	625	mW
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	-65 ~ 150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	V_{CB}=-20V, I_E=0	-	-	-100	nA
Emitter Cut-off Current		I_{EBO}	V_{EB}=-5V, I_C=0	-	-	-10	μA
Collector-Emitter Breakdown Voltage	TBC327	$V_{(BR)CEO}$	I_C=-10mA, I_B=0	-45	-	-	V
	TBC328			-25	-	-	
DC Current Gain		$h_{FE(1)}$ (Note)	V_{CE}=-1V, I_C=-100mA	100	-	400	
		$h_{FE(2)}$	V_{CE}=-1V, I_C=-500mA	40	-	-	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	I_C=-500mA, I_B=-50mA	-	-	-0.7	V
Base-Emitter Voltage		V_{BE}	V_{CE}=-1V, I_C=-500mA	-	-	-1.2	V
Transition Frequency		f_T	V_{CE}=-5V, I_C=-10mA, f=35MHz	-	100	-	MHz
Collector Output Capacitance		C_{ob}	V_{CB}=-10V, f=1MHz	-	22	-	pF

Note: $h_{FE(1)}$ Classification 327-A , 328-A : 100 ~ 250
327-B , 328-B : 160 ~ 400